

Silicon NPN Power Transistors

2N3235

DESCRIPTION

- With TO-3 package
- Excellent safe operating area
- Low collector saturation voltage

APPLICATIONS

- Designed for general-purpose switching and amplifier applications.

PINNING

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

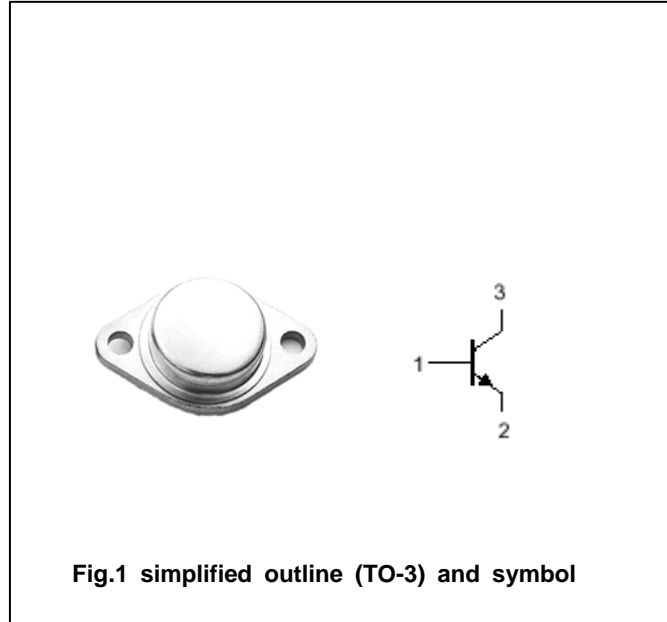


Fig.1 simplified outline (TO-3) and symbol

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	65	V
V_{CEO}	Collector-emitter voltage	Open base	55	V
V_{EBO}	Emitter-base voltage	Open collector	7	V
I_C	Collector current		15	A
I_B	Base current		7	A
P_C	Collector power dissipation	$T_C=25^\circ\text{C}$	115	W
T_j	Junction temperature		150	$^\circ\text{C}$
T_{stg}	Storage temperature		-65~200	$^\circ\text{C}$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
$R_{(th) jc}$	Thermal resistance junction to case	1.52	$^\circ\text{C}/\text{W}$

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CHARACTERISTICS

 $T_j=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-emitter sustaining voltage	$I_C=0.2A ; I_B=0$	55			V
$V_{CE(sat)-1}$	Collector-emitter saturation voltage	$I_C=4A ; I_B=0.4A$			1.1	V
$V_{CE(sat)-2}$	Collector-emitter saturation voltage	$I_C=10A ; I_B=3.3A$			3.0	V
$V_{BE(on)}$	Base-emitter on voltage	$I_C=5A ; V_{CE}=5V$			1.5	V
I_{CEO}	Collector cut-off current	$V_{CE}=30V ; I_B=0$			0.7	mA
I_{CBO}	Collector cut-off current	$V_{CB}=65V ; I_E=0$			0.1	mA
I_{EBO}	Emitter cut-off current	$V_{EB}=7V ; I_C=0$			0.1	mA
h_{FE-1}	DC current gain	$I_C=5A ; V_{CE}=5V$	20		70	
h_{FE-2}	DC current gain	$I_C=10A ; V_{CE}=5V$	5			

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PACKAGE OUTLINE

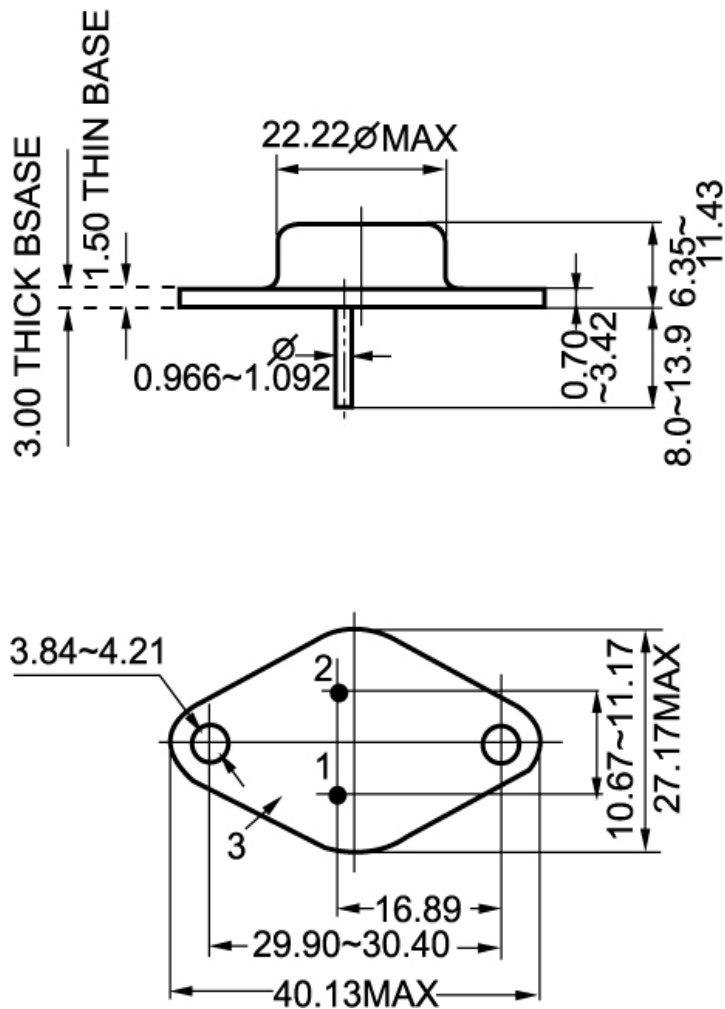


Fig.2 outline dimensions (unindicated tolerance: $\pm 0.1\text{mm}$)